

ABSTRACT

A new method is provided for exposing a semiconductor surface over which a photoresist mask has been created to elevated temperatures. Using conventional methods of wafer temperature exposure, the wafer is mounted on the surface of a hot plate with the active surface of the wafer, over which the photoresist mask has been created, facing upwards. The invention provides a method whereby the conventional upward position of the wafer during temperature exposure is changed. The wafer is, during temperature exposure, placed on the surface of a hot plate, the hot plate is then positioned under an angle with a horizontal direction and may, under the invention, be turned such that the active surface of the wafer, over which a photoresist mask has been formed, faces downwards.